

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	168016	gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:51
L2	2141	1 and (electron adj microscope)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:51
L3	9	2 and (induced adj current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:55
L4	168	2 and (secondary adj electrons)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 11:56
L5	35	4 and (gate adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 12:08
L6	34	hamada-takehiko-.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 12:10
L7	0	((position near (detecting or detection)) and (electron adj beam) and (contact near hole) and voltage and current and silicon and (gate adj electrode) and (gate adj oxide)). clm.	US-PGPUB	OR	ON	2005/10/27 12:15